

High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

IXBT16N360HV IXBH16N360HV



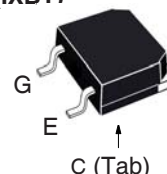
$$V_{CES} = 3600V$$

$$I_{C110} = 16A$$

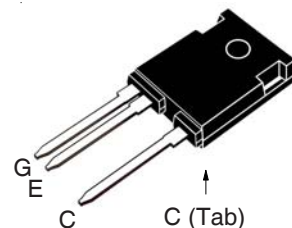
$$V_{CE(sat)} \leq 3.0V$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	3600	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	3600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	48	A
I_{C110}	$T_C = 110^\circ C$	16	A
I_{CM}	$T_C = 25^\circ C$, 1ms	72	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 25\Omega$ Clamped Inductive Load	$I_{CM} = 60$ $V_{CES} \leq 1500$	A V
T_{SC} (SCSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 82\Omega$, $V_{CE} = 1500V$, Non-Repetitive	10	μs
P_C	$T_C = 25^\circ C$	270	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-247HV)	1.13/10	Nm/lb.in
Weight	TO-268HV	4	g
	TO-247HV	6	g

TO-268HV (IXBT)



TO-247HV (IXBH)



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- High Voltage Packages
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	3600		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			10 μA 500 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 16A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		2.5 3.1	3.0 V V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 16\text{A}, V_{CE} = 10\text{V}$, Note 1	7	12	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1116	pF
C_{oes}			60	pF
C_{res}			25	pF
$Q_{g(on)}$	$I_C = 16\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1.5\text{KV}$		65	nC
Q_{ge}			7	nC
Q_{gc}			30	nC
$t_{d(on)}$	Resistive load, $T_J = 25^\circ\text{C}$		30	ns
t_r		$I_C = 16\text{A}, V_{GE} = 15\text{V}$	260	ns
$t_{d(off)}$	$V_{CE} = 1.5\text{KV}, R_G = 25\Omega$		184	ns
t_f			110	ns
$t_{d(on)}$	Resistive load, $T_J = 125^\circ\text{C}$		36	ns
t_r		$I_C = 16\text{A}, V_{GE} = 15\text{V}$	385	ns
$t_{d(off)}$	$V_{CE} = 1.5\text{KV}, R_G = 25\Omega$		190	ns
t_f			115	ns
R_{thJC}	TO-247HV			0.46 $^\circ\text{C/W}$
R_{thCS}			0.21	$^\circ\text{C/W}$

Reverse Diode

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max
V_F	$I_F = 16\text{A}, V_{GE} = 0\text{V}$, Note 1			3.5 V
t_{rr}	$I_F = 16\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		620	ns
I_{RM}		$V_R = 100\text{V}, V_{GE} = 0\text{V}$	21.5	A
Q_{RM}			6.7	μC

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

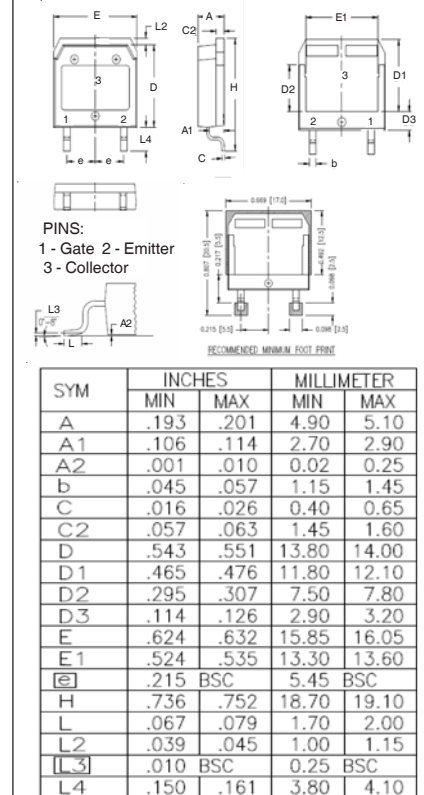
ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338 B2
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

TO-268HV Outline



TO-247HV Outline

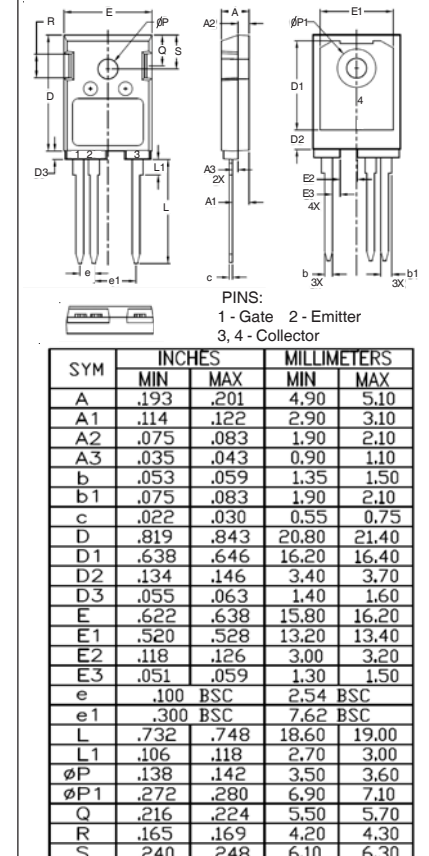


Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

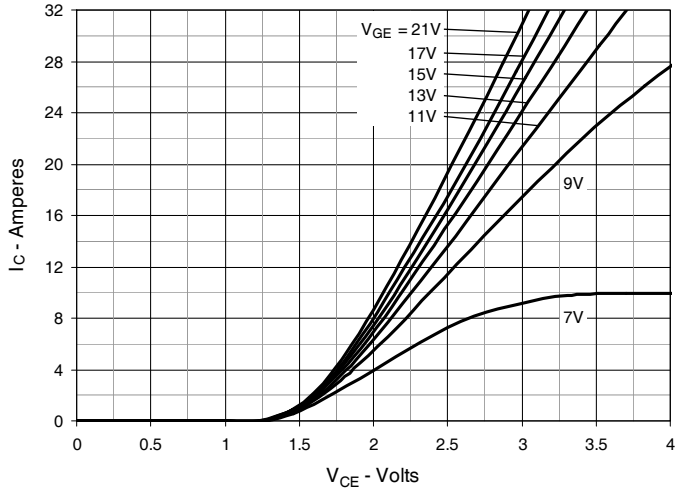


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

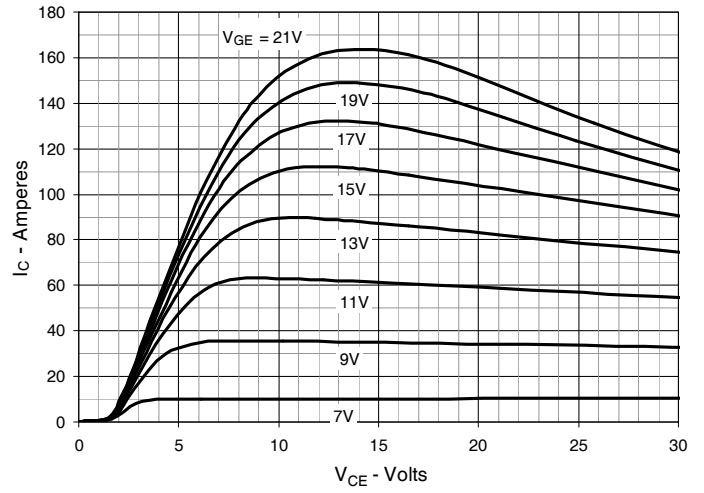


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

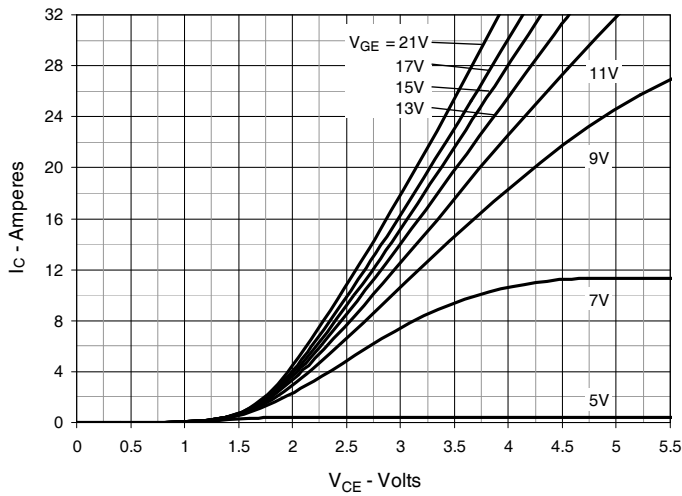


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

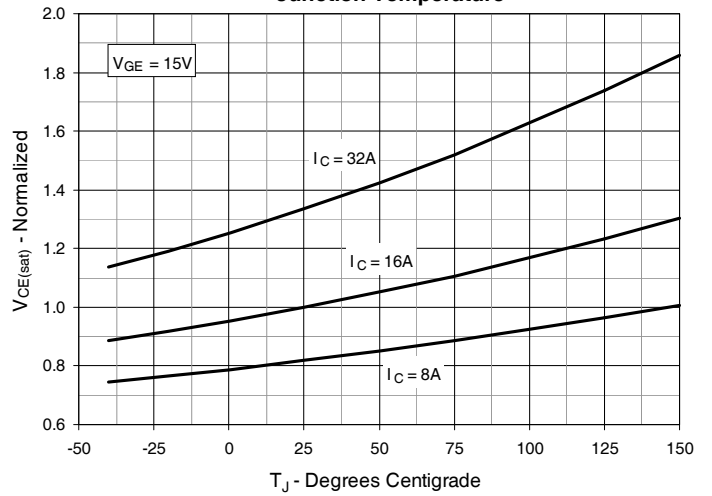


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

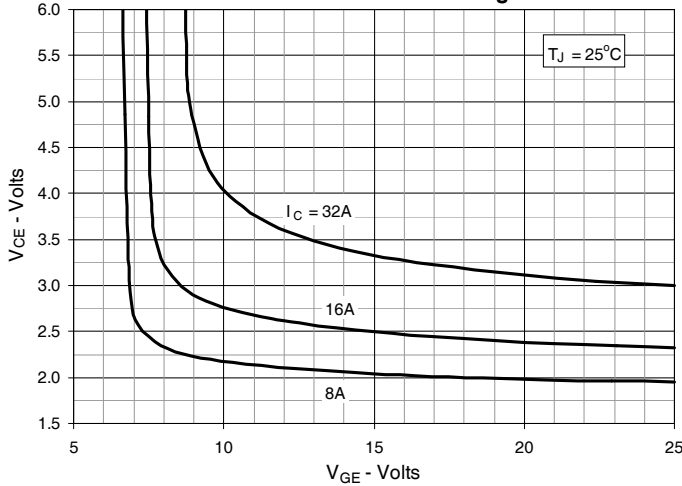


Fig. 6. Input Admittance

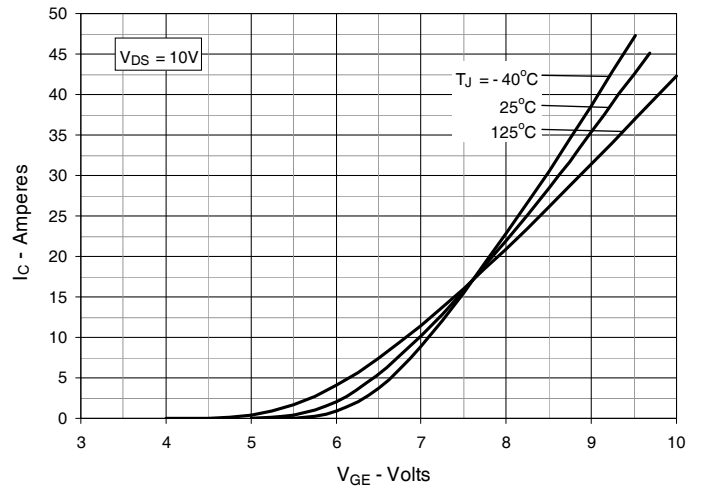


Fig. 7. Transconductance

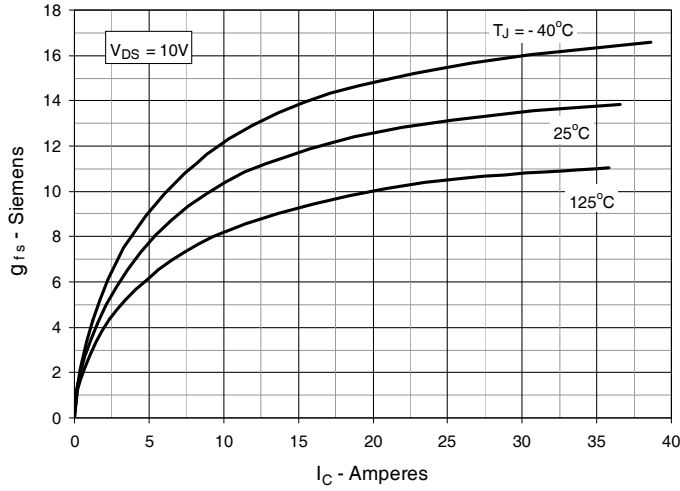


Fig. 8. Forward Voltage Drop of Intrinsic Diode

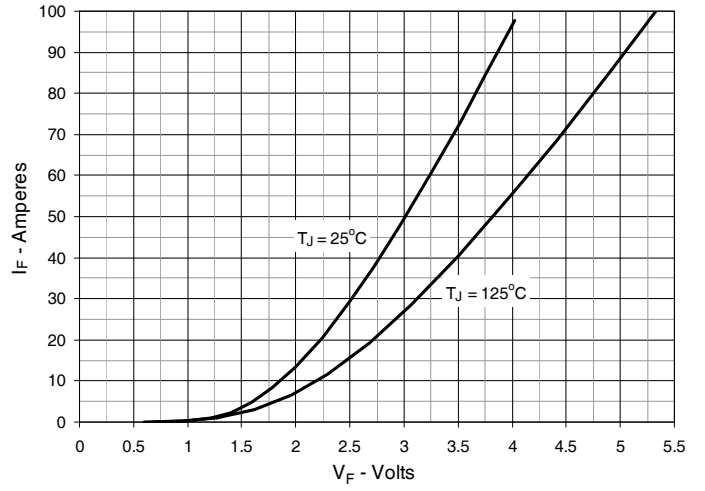


Fig. 9. Gate Charge

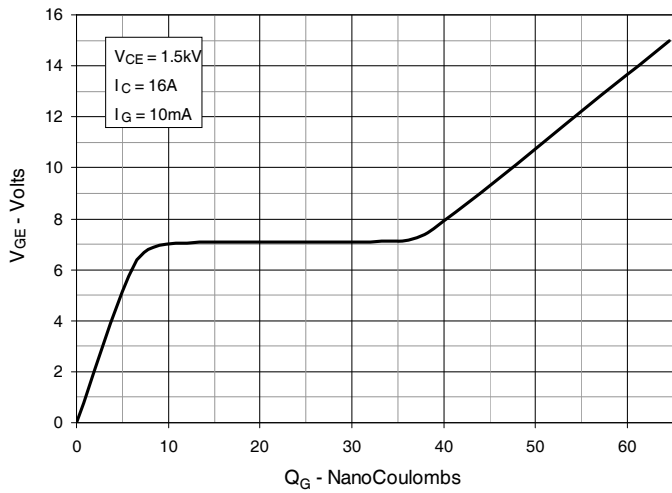


Fig. 10. Capacitance

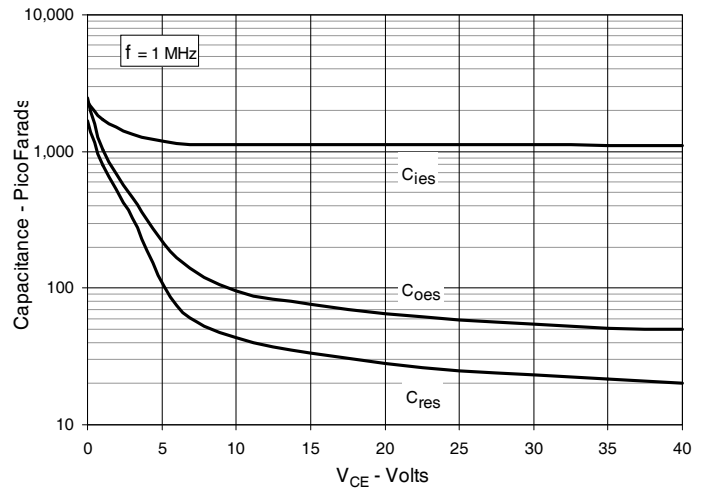


Fig. 11. Reverse-Bias Safe Operating Area

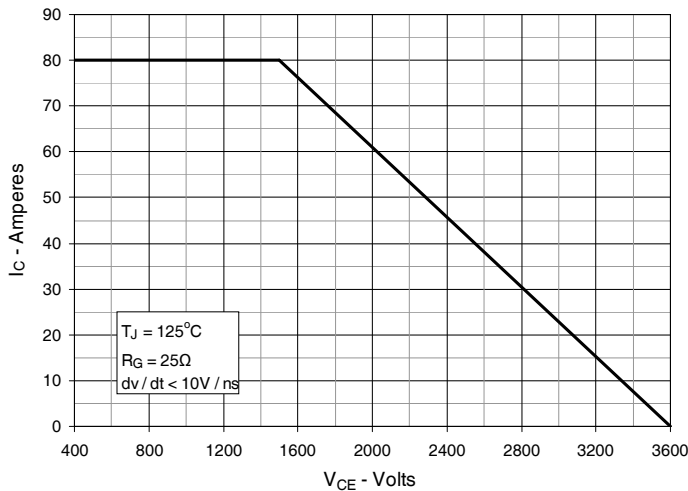


Fig. 12. Maximum Transient Thermal Impedance

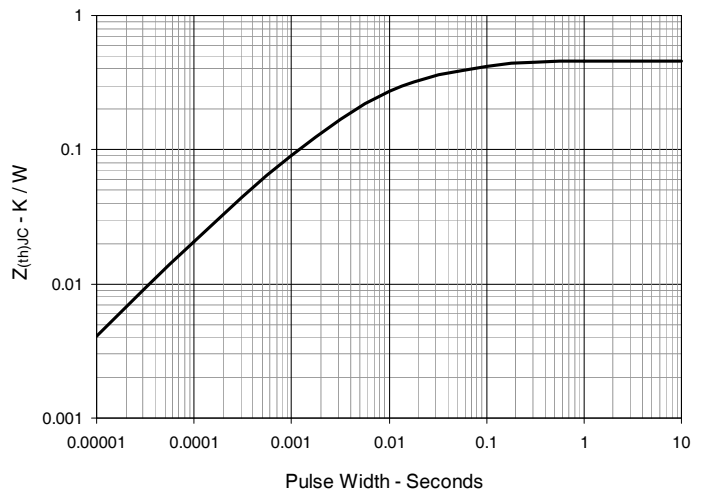


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

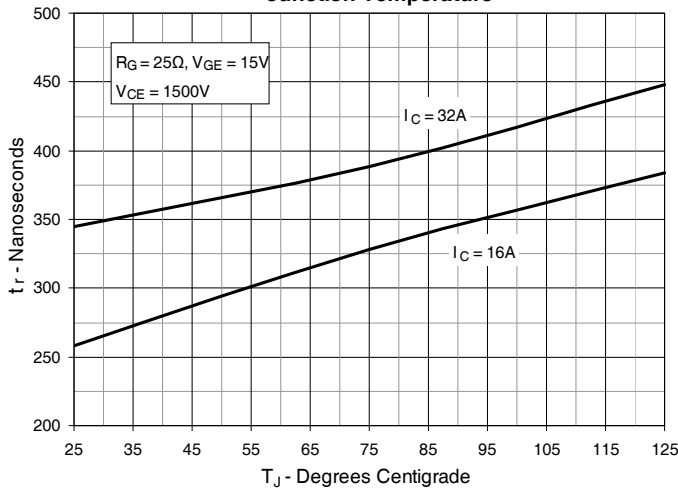


Fig. 14. Resistive Turn-on Rise Time vs. Collector Current

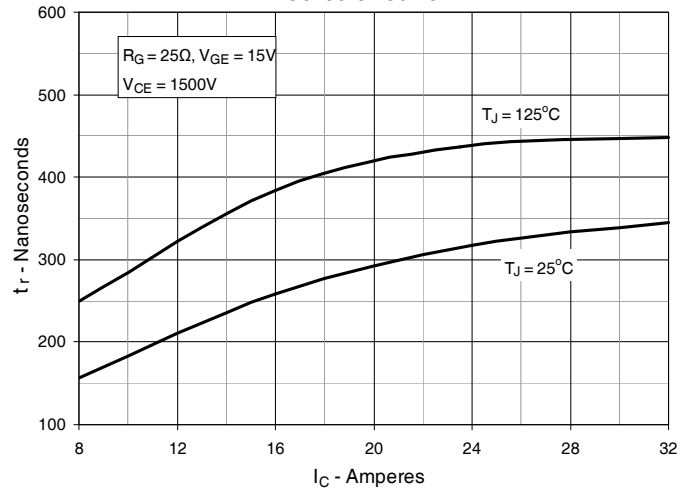


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

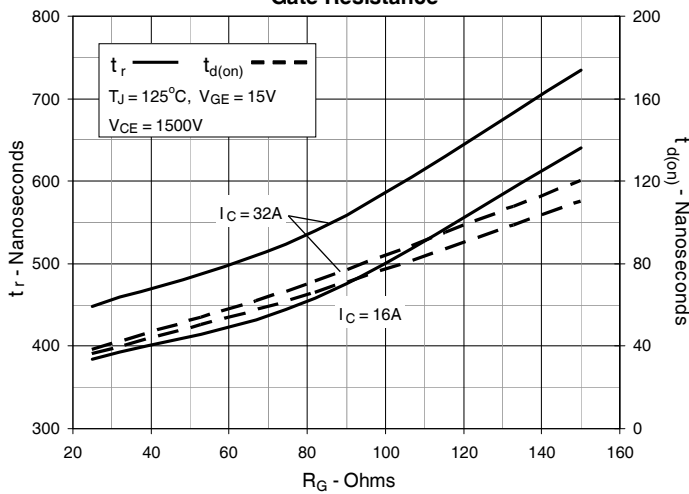


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

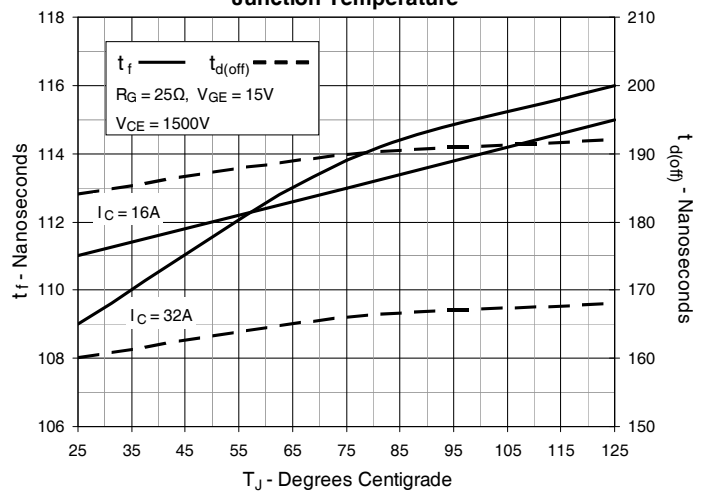


Fig. 17. Resistive Turn-off Switching Times vs. Collector Current

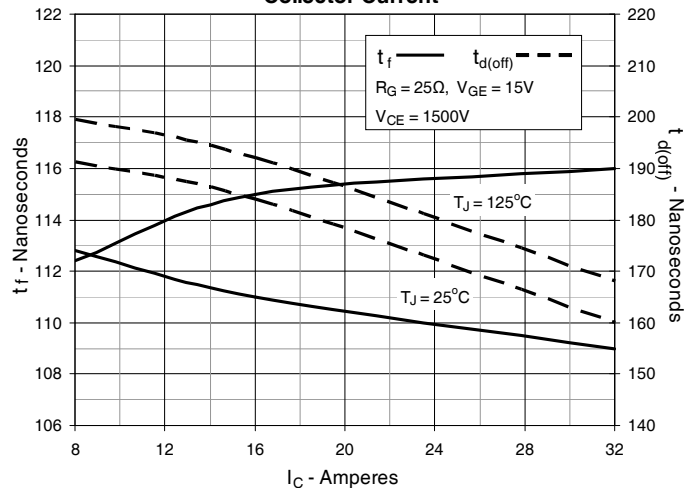


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

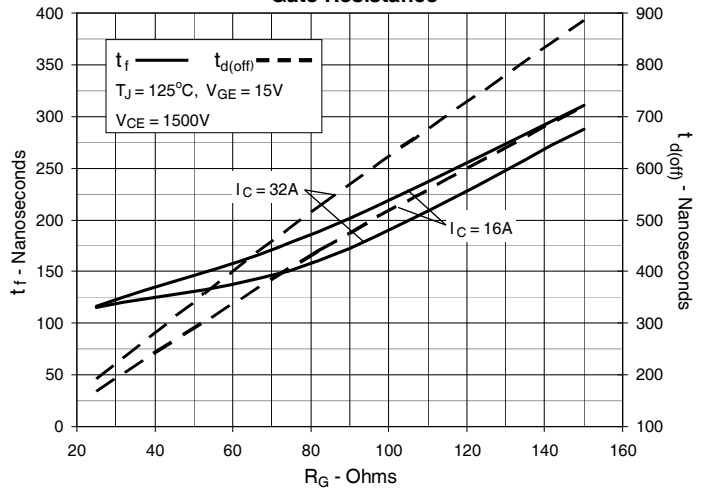


Fig. 19. Forward-Bias Safe Operating Area @ $T_C = 25^\circ\text{C}$

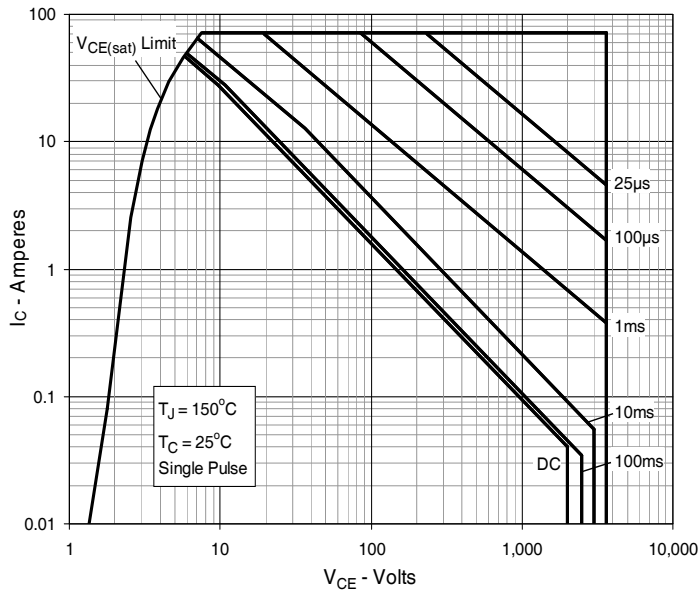
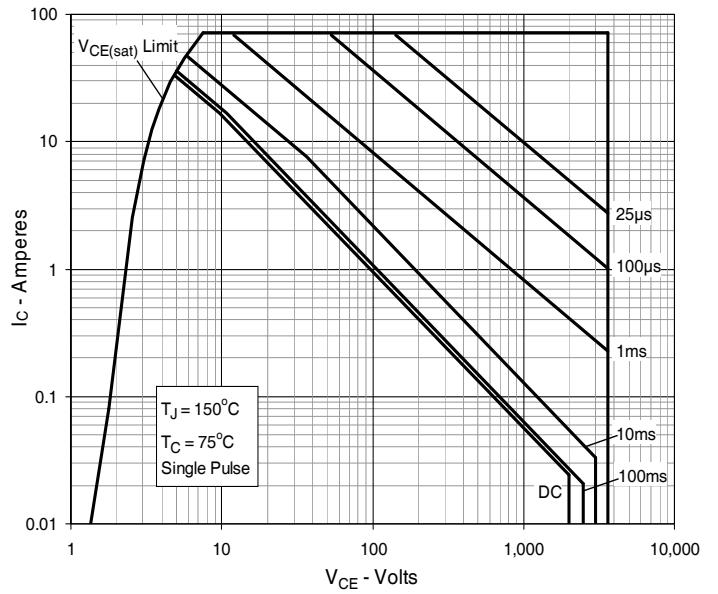


Fig. 20. Forward-Bias Safe Operating Area @ $T_C = 75^\circ\text{C}$





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